

Congratulations to the 26 Newly Elected IEEE Electron Devices Society Fellows

Effective January 1, 2017

Hugh Barnaby, Arizona State University, Tempe, Arizona, USA
for research of radiation effects in bipolar junction transistors

Yu Cao, Arizona State University, Tempe, Arizona, USA
for development of predictive technology models for reliable circuit and system integration

Edoardo Charbon, Delft University of Technology, Delft, Netherlands
for contributions to solid-state single photon avalanche detectors and their applications in imaging

Wei-ting Chien, SMIC-Semiconductor Mfg. Int'l Corp., Shanghai, China
for leadership in reliability management

Terry Ericson, Ericson Innovations LLC, Annapolis, Maryland, USA
for leadership in power electronics

Christopher Hierold, Swiss Federal Institute of Technology, Zurich, Switzerland
for contributions to microelectromechanical sensors and microthermoelectric energy harvesting

Ru Huang, Peking University, Beijing, China
for contributions to multi-gate silicon nanowire transistor technology

Tian-wei Huang, National Taiwan University, Taipei, Taiwan
for contributions to design and development of millimeter-wave CMOS RFICs

Chia-hong Jan, Intel Corporation, Portland, Oregon, USA
for leadership in developing low power logic technologies for System-on-Chip

Quanxi Jia, University of Buffalo, Buffalo, New York, USA
for contributions to coated superconductors and metal-oxide thin films for electronic applications

Hongrui Jiang, University of Wisconsin, Madison, Wisconsin, USA
for contributions to materials and micro-scale optical tools for medical imaging

Richard King, Arizona State University, Tempe, Arizona, USA
for contributions to high-performance space and terrestrial photovoltaics technology

Hulya Kirkici, Auburn University, Auburn, Alabama, USA
for contributions to high frequency, high field dielectric breakdown and electrical insulation for space and aerospace power systems

Steven Koester, University of Minnesota, Minneapolis, Minnesota, USA
for contributions to group-IV electronic and photonic devices

Xiuling Li, University of Illinois, Champaign, Illinois, USA

for contributions to semiconductor nanomaterials for electronic and photonic applications

Donald Y. Lie, Texas Tech University, Lubbock, Texas, USA

for contributions to high linearity and high efficiency silicon RF power amplifiers for broadband wireless applications

Theresa Mayer, Virginia Tech, Blacksburg, Virginia, USA

for contributions to nanomaterials integration and directed assembly

Junichi Nakamura, Brillnics Japan Inc., Tokyo, Japan

for leadership in CMOS image sensors

Borivoje Nikolic, University of California, Berkeley, California, USA

for contributions to energy-efficient design of digital and mixed-signal circuits

Akihiro Nitayama, Tohoku University, Sendai, Japan

for leadership in 3-dimensional NAND Flash memory technology development

Tomas Palacios, Massachusetts Institute of Technology, Cambridge, Massachusetts, USA

for contributions to gallium nitride electron devices and two-dimensional materials

Dimitrios Peroulis, Purdue University, West Lafayette, Indiana, USA

for contributions to MEMS-based tunable filters

Ramgopal Raovalipe, Indian Institute of Technology, Powai, Mumbai, India

for contributions to CMOS System-on-Chip technologies

Andrei Vladimirescu, Berkeley Wireless Research Center, Berkeley, California, USA

for contributions to the development and commercial adoption of SPICE circuit simulation

Sorin Voinigescu, University of Toronto, Toronto, Ontario, Canada

for contributions to silicon and silicon-germanium microwave and millimeter-wave devices and integrated circuits

Xin Zhang, Boston University, Boston, Massachusetts, USA

for contributions to microelectromechanical systems

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